

AMENDMENTS TO THE SPECIFICATION

Please add the following new paragraph on page 9 at line 2 as follows:

Fig. 7 is a schematic representation of an exemplary group III nitride semiconductor light-emitting device according to the present invention.

Please add the following new paragraph on page 9 after line 3, at the beginning of the section “Best Mode for Carrying Out the Invention”, as follows:

Fig. 7 is a schematic representation showing a general structure of an exemplary group III nitride semiconductor light-emitting device according to the present invention, including an n-type layer 21, a p-type layer 23, light emitting layer 22, a negative electrode 24, and a positive electrode 27. In Fig. 7, positive electrode 27 is composed of translucent electrode 25 and pad electrode 26.